



DMN2990UDJQ

### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
20V	0.99Ω @ V <sub>GS</sub> = 4.5V	450mA
	1.2Ω @ V <sub>GS</sub> = 2.5V	400mA
	1.8Ω @ V <sub>GS</sub> = 1.8V	330mA
	2.4Ω @ V <sub>GS</sub> = 1.5V	300mA

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

### Features

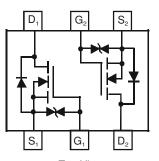
- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package 1mm x 1mm
- Low Package Profile, 0.45mm Maximum Package Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.027 grams (Approximate)







Top View Schematic and Transistor Diagram

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMN2990UDJQ-7	SOT963	10K/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

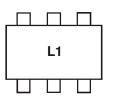
See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>

<1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



L1 = Product Type Marking Code



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 6) $V_{GS}$ = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	450 350	mA
Continuous Drain Current (Note 6) $V_{GS}$ = 1.8V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	330 220	mA
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	800	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	350	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	360	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = $\pm 25^{\circ}$ C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	,						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zara Cata Valtaga Drain Current @T05%	1	-	-	50	nA	$V_{DS} = 5V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C	IDSS	-	-	100		$V_{DS} = 16V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	-	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		-	0.60	0.99		$V_{GS} = 4.5V, I_D = 100mA$	
		-	0.75	1.2		$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	0.90	1.8	Ω	$V_{GS} = 1.8V, I_D = 20mA$	
		-	1.2	2.4		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA	
		-	2.0	-		$V_{GS} = 1.2V, I_{D} = 1mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	180	-	-	ms	$V_{DS} = 10V, I_D = 400mA$	
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-	0.6	1.0	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	27.6	-	pF		
Output Capacitance	C <sub>oss</sub>	-	4.0	-	рF	− V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	2.8	-	pF	1 = 1.000112	
Total Gate Charge	Qg	-	0.5	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 250mA$	
Gate-Source Charge	Q <sub>qs</sub>	-	0.07	-	nC		
Gate-Drain Charge	Q <sub>qd</sub>	-	0.07	-	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.0	-	ns		
Turn-On Rise Time	t <sub>R</sub>	-	3.3	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	19.0	-	ns	$R_{L} = 47\Omega, R_{g} = 10\Omega,$	
Turn-Off Fall Time	t <sub>F</sub>	-	6.4	-	ns	$-I_D = 200 \text{mA}$	

Notes: 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.

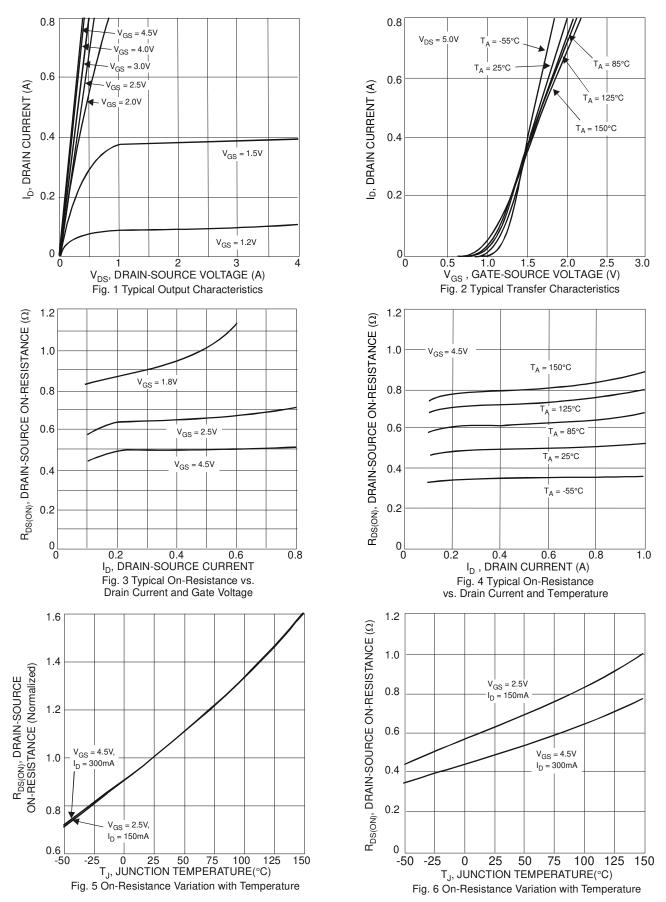
7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

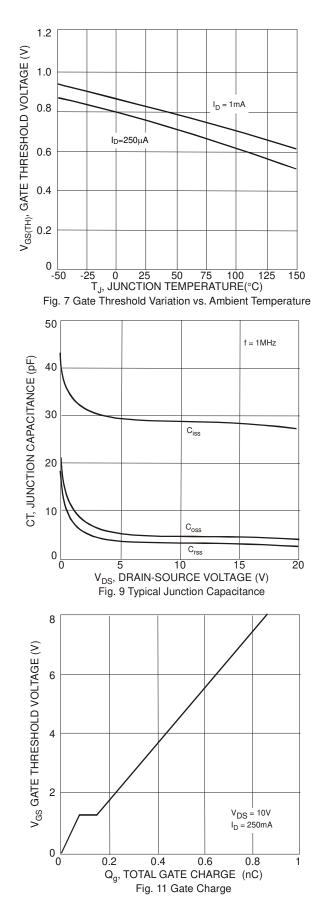


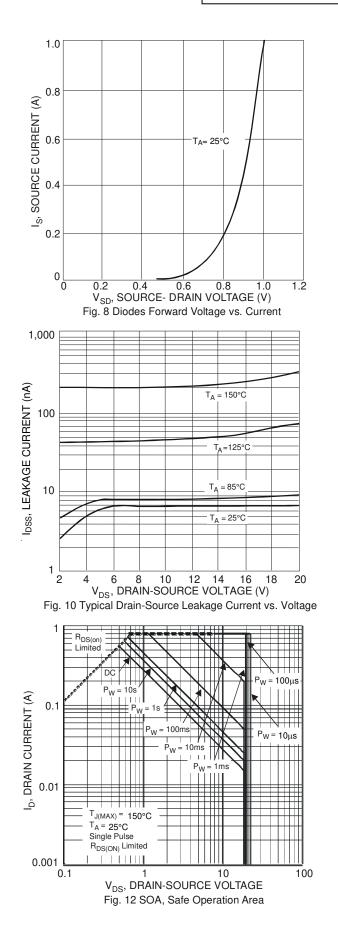
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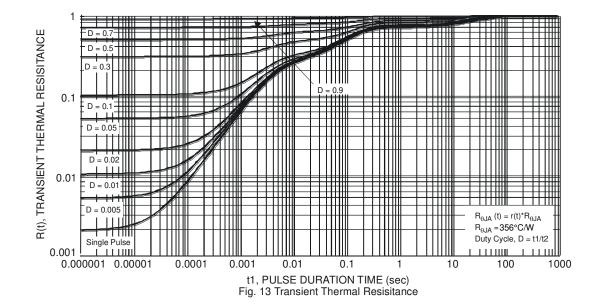


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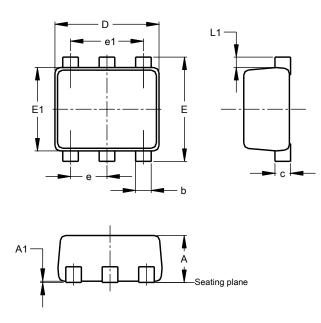




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

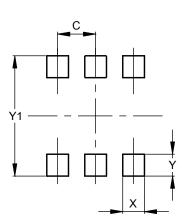
### SOT963



SOT963						
Dim	Min	Max	Тур			
Α	0.40	0.50	0.45			
A1	0.00	0.05				
b	0.10	0.20	0.15			
С	0.120	0.180	0.150			
D	0.95	1.05	1.00			
Е	0.95	1.05	1.00			
E1	0.75	0.85	0.80			
е			0.35			
e1			0.70			
L1	0.05	0.15	0.10			
All Dimensions in mm						

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	0.350			
Х	0.200			
Y	0.200			
Y1	1.100			

SOT963



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